

GERMANIUM DIODE

Germanium diode in subminiature all glass DO-7 envelope, intended for switching applications.

RATINGS (Limiting values)

		$T_{amb} = 75\text{ }^{\circ}\text{C}$
Continuous reverse voltage	V_R	max. 15 V
Repetitive peak reverse voltage	V_{RRM}	max. 15 V
Non repetitive peak reverse voltage ($t < 1\text{ s}$)	V_{RSM}	max. 20 V
Average forward current	I_{FAV}	max. 7 mA
Forward current (d.c.)	I_F	max. 10 mA
Repetitive peak forward current	I_{FRM}	max. 50 mA
Non repetitive peak forward current ($t < 1\text{ s}$)	I_{FSM}	max. 100 mA
Operating ambient temperature	T_{amb}	max. 75 $^{\circ}\text{C}$
Storage temperature	T_{stg}	-55 to +90 $^{\circ}\text{C}$

THERMAL RESISTANCE

From junction to ambient	$R_{th\ j-a}$	=	0.55 $^{\circ}\text{C}/\text{mW}$
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CHARACTERISTICS

Forward voltage at $T_{amb} = 25\text{ }^{\circ}\text{C}$

$I_F = 3\text{ mA}$

V_F	typ.	0.55 V
		0.30 to 1.00 V

Reverse current at $T_{amb} = 60\text{ }^{\circ}\text{C}$

$V_R = 15\text{ V}$

I_R	typ.	40 μA
	<	155 μA

Reverse recovery current when switched from $I_F = 5\text{ mA}$ to $V_R = 5\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$ measured at $t_{rr} = 0.5\text{ }\mu\text{s}$

I_R	typ.	80 μA
	<	300 μA

measured at $t_{rr} = 3.5\text{ }\mu\text{s}$

I_R	typ.	15 μA
	<	60 μA

Diode capacitance at $f = 0.5\text{ MHz}$

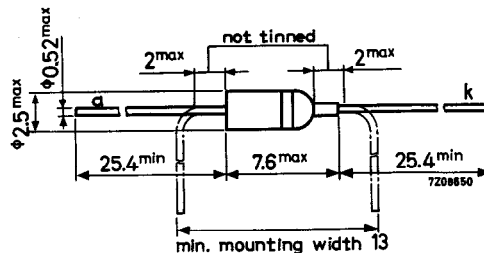
$V_R = 0.75\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$

C_d	<	0.5 pF
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MECHANICAL DATA

Dimensions in mm

DO-7



The coloured band indicates the cathode side

